

## 参数表

**2CL15KV/1A** 高压硅堆采用高可靠性的台面结构及扩散工艺，环氧树脂真空灌注密闭封装。

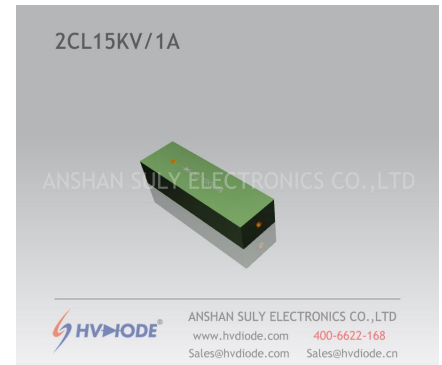
**2CL15KV/1A** High voltage silicon assembly adopts high reliable mesa structure with the diffusion craft work, and epoxy resin molded in a compact structure.

### ▼ 产品特点 Feature

- ❖ 雪崩电压击穿保护特性 **Avalanche Characteristic**
- ❖ 优异的抗浪涌电流冲击特性 **Excellent surge current resistance**
- ❖ 高速开关响应特性 **High speed switch response characteristics**
- ❖ 采用新型环氧树脂真空封装技术，表面具有抗腐蚀性  
**Epoxy resin molded in vacuum, have anticorrosion in the surface**
- ❖ 工作结温 -50°C—+175°C **Tj:50°C—+175°C**
- ❖ 特殊耐高温性能芯片，可承受严酷恶劣的使用条件
- ❖ **Special high temperature resistant chip that can withstand harsh working conditions**

### ▼ 产品 2D 图示

#### Graphical Representation

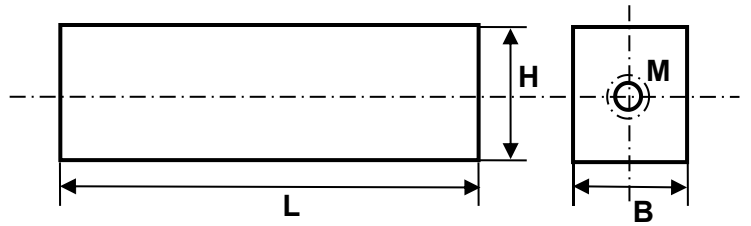


	参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	数值 Rating
Absolute Maximum Ratings 极限值 (绝对最大值)	反向重复峰值电压 Repetitive Peak Reverse Voltage	$V_{RRM}$	KV	Ta=25°C $I_R=2.0\mu A$	15
	反向工作峰值电压) Peak Working Reverse Voltage	$V_{RWM}$	KV	Ta=25°C $I_R=2.0\mu A$	15
	正向平均电流 Average Forward Current	$I_{F(AV)}$	A	正弦半波 50Hz, 电阻负载, $T_{break}=50^\circ C$ ( 50Hz Half-sine Wave , Resistance load @ $T_{break}=50^\circ C$ )	1
	反向恢复时间 Reverse Recovery Time	trr	nS		--
	正向(不重复)浪涌电流 Surge Forward Current	$I_{FSM}$	A	正弦半波持续时间 0.01S 50Hz 0.01S @ Half-Sine wave 50Hz	40
	工作环境温度 Operating Ambient Temperature	$T_a$	°C		-55 ~ +175
	存储温度 Storage Temperature	$T_{stg}$	°C		-40 ~ +125
Electrical Characteristics 电特性	正向峰值电压 Forward Peak Voltage	$V_{FM}$	V	@ Ta=25°C $I_F=1A$	18
	反向峰值电流 Peak Reverse Current	$I_{RRM1}$	$\mu A$	@ Ta=25°C $V_{RM}=V_{RRM}$	2.0
		$I_{RRM2}$	$\mu A$	@ Ta=100°C $V_{RM}=V_{RRM}$	20.0

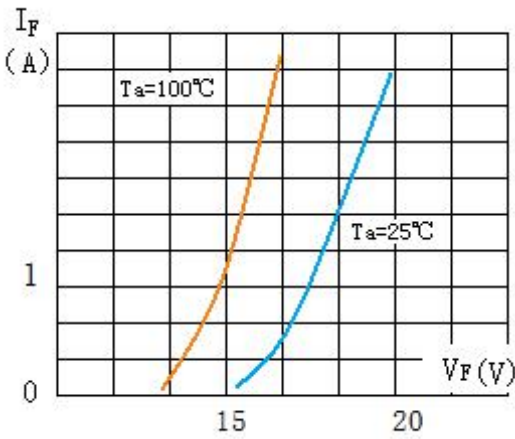
▼ 外形尺寸图示 Outline Drawings

(单位：毫米 mm)

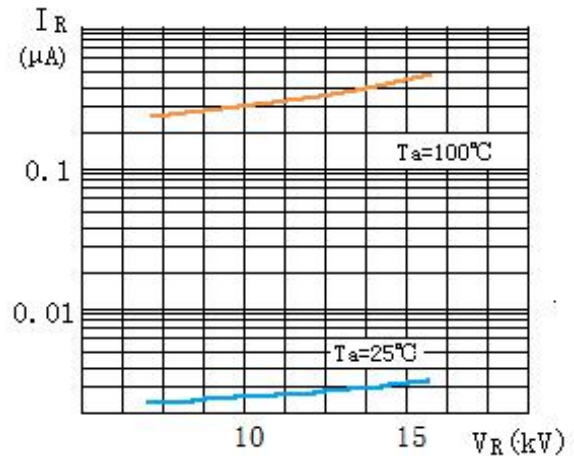
尺寸/图号	长 (L)	宽 (W)	高 (H)	电极 (M)
Fig①	100	25	18	5*2 4*1
Fig②	100	30	20	5*2 4*1



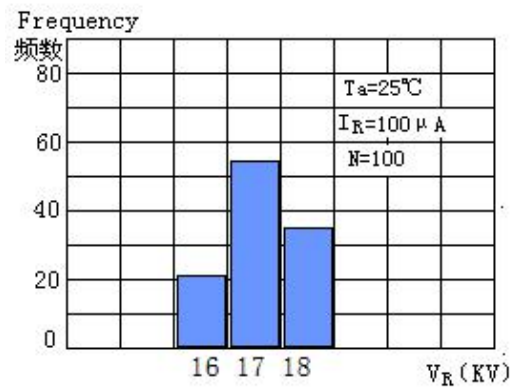
▼ 特性曲线图 Characteristic Curve



正向特性曲 ( 2CL15KV/1A )  
Forward Characteristics



反向特性曲线 ( 2CL15KV/1A )  
Reverse Characteristics



反向雪崩电压分布 ( 2CL15KV/1A )  
Avalanche Breakdown Voltage Distribution